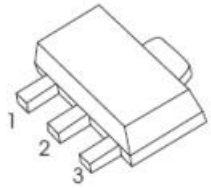
安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO. , LTD.

BSR33

SOT-89 Bipolar Transistor 双极型三极管



■Features 特点

PNP General Purpose 通用

■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-90	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-80	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-1000	mA
Power dissipation 耗散功率	$P_C(T_a=25℃)$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\Theta JA}$	250	℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	-55to+150℃	

■Device Marking 产品打标

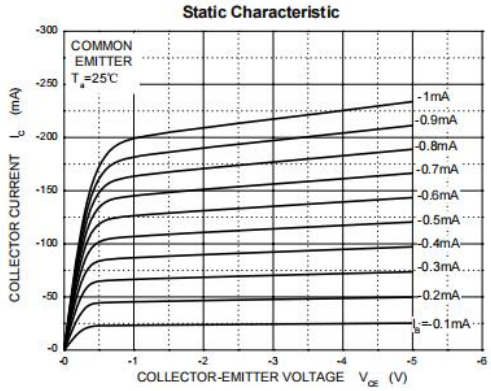
BSR33=BR4

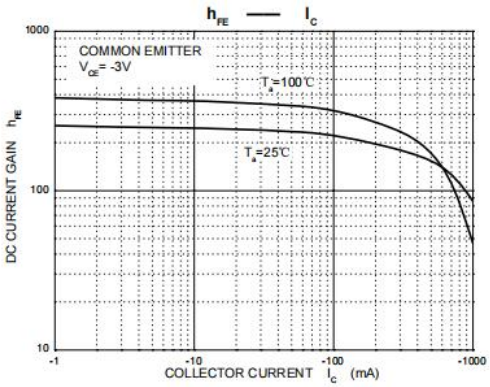
■Electrical Characteristics 电特性

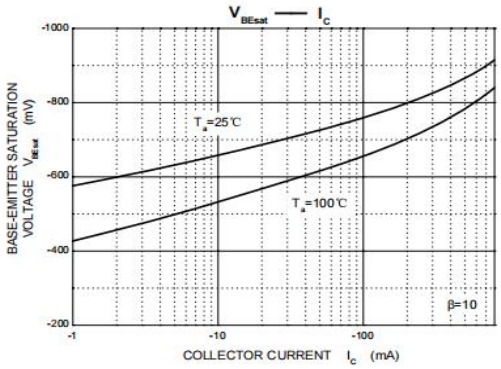
(T_A=25℃ unless otherwise noted 如无特殊说明，温度为 25℃**)**

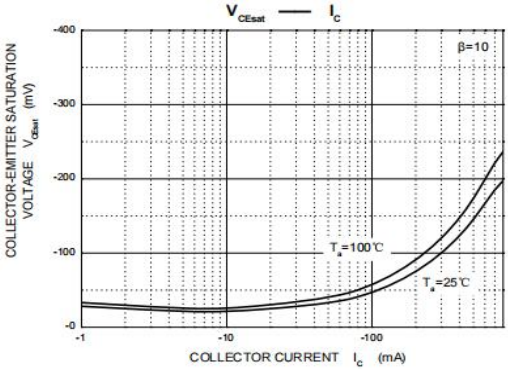
Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(I_C= -100μA，I_E=0)	BV_{CBO}	-90	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I_C= -1mA，I_B=0)	BV_{CEO}	-80	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(I_E= -100μA，I_C=0)	BV_{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V_{CB}= -60V，I_E=0)	I_{CBO}	—	—	-0.1	μA
Emitter-Base Leakage Current 发射极基极漏电流(V_{EB}= -5V，I_C=0)	I_{EBO}	—	—	-0.1	μA
DC Current Gain(V_{CE}= -5V，I_C= -100mA) 直流电流增益(V_{CE}= -5V，I_C= -500mA)	H_{FE}	100 50	—	300	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I_C= -500mA，I_B= -50mA)	$V_{CE(sat)}$	—	—	-0.5	V
Base-Emitter Saturation Voltage 基极发射极饱和压降(I_C= -500mA，I_B= -50mA)	$V_{BE(sat)}$	—	—	-1.2	V
Base-Emitter On Voltage 基极发射极导通电压(V_{CE}= -10V，I_C= -500mA)	$V_{BE(on)}$	—	—	-1.2	V
Transition Frequency 特征频率(V_{CE}= -10V，I_C= -50mA)	f_T	—	100	—	MHz
Output Capacitance 输出电容(V_{CB}= -10V，I_E=0, f=1MHz)	Cob	—	26	—	pF

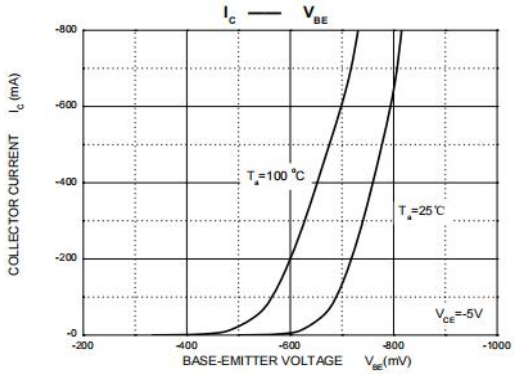
■Typical Characteristic Curve 典型特性曲线

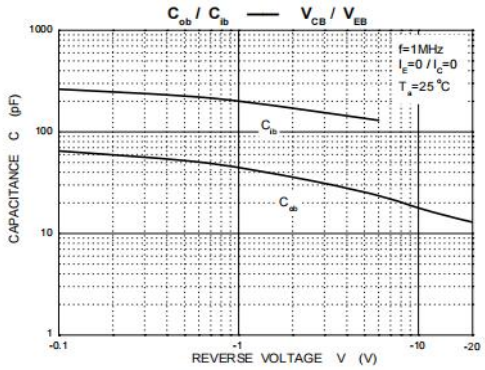


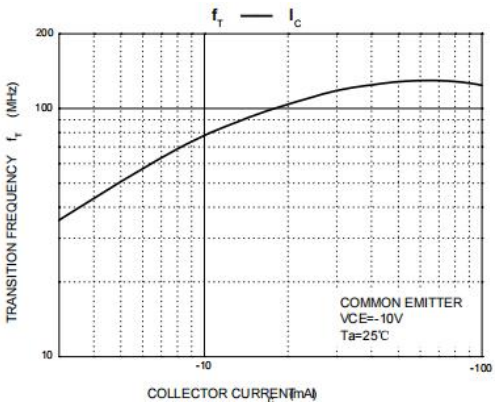


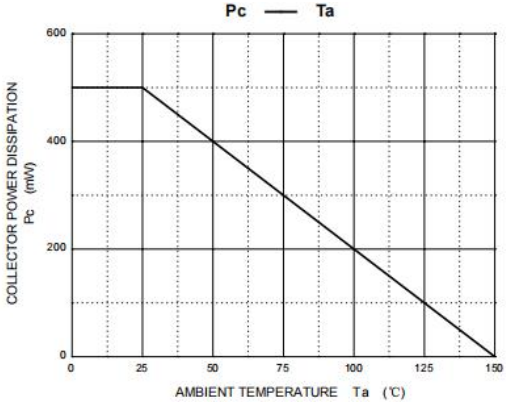




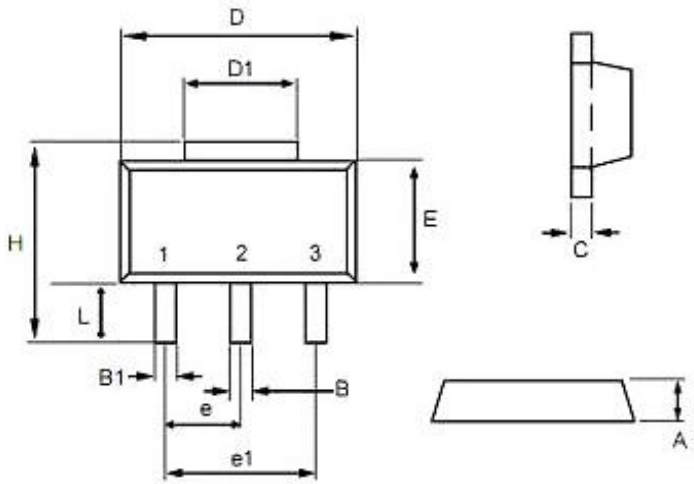








■**Dimension** 外形封装尺寸



Dim	min	max
A	1.40	1.60
B	0.40	0.56
B1	0.35	0.48
C	0.35	0.44
D	4.40	4.60
D1	1.35	1.83
e	1.50 BSC	
e1	3.00 BSC	
E	2.29	2.60
H	3.75	4.25
L	0.80	1.20